Designer's™ Data Sheet

SWITCHMODETM

NPN Bipolar Power Transistor For Switching Power Supply Applications

The MJE/MJF18002 have an applications specific state-of-the-art die designed for use in 220 V line operated Switchmode Power supplies and electronic light ballasts. These high voltage/high speed transistors offer the following:

- Improved Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain hff
 - Fast Switching
 - No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Tight Parametric Distributions are Consistent Lot-to-Lot
- Two Package Choices: Standard TO-220 or Isolated TO-220
- MJF18002, Case 221D, is UL Recognized at 3500 V_{RMS}: File #E69369

MAXIMUM RATINGS

Rating	I	Symbol	MJE18002	MJF18002	Unit
Collector–Emitter Sustainin	VCEO	450		Vdc	
Collector–Emitter Breakdov	vn Voltage	VCES	1000		Vdc
Emitter-Base Voltage		V _{EBO}	9.	9.0	
Collector Current — Contin — Peak(1	I _C	2.0 5.0		Adc	
Base Current — Continuous — Peak(1)	I _B I _{BM}	1.0 2.0		Adc	
RMS Isolated Voltage(2) (for 1 sec, R.H. < 30%, T _C = 25°C)	Test No. 1 Per Fig. 1 Test No. 2 Per Fig. 2 Test No. 3 Per Fig. 3	VISOL	_ _ _	4500 3500 1500	V
Total Device Dissipation Derate above 25°C	(T _C = 25°C)	PD	50 0.4	25 0.2	Watts W/°C
Operating and Storage Tem	TJ, T _{stg}	−65 t	o 150	°C	

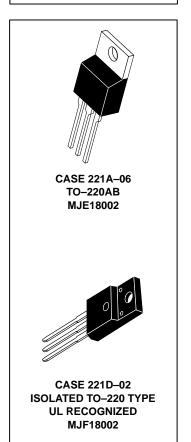
THERMAL CHARACTERISTICS

Rating	Symbol	MJE18002	MJF18002	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	$R_{ heta JC}$	2.5 62.5	5.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	26	60	°C

MJE18002* MJF18002*

*Motorola Preferred Device

POWER TRANSISTOR
2.0 AMPERES
1000 VOLTS
25 and 50 WATTS



IEBO

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (I _C = 100 mA, L = 25 mH)	V _{CEO(sus)}	450			Vdc
Collector Cutoff Current (V _{CE} = Rated V _{CEO} , I _B = 0)	ICEO	_		100	μAdc
Collector Cutoff Current (V_{CE} = Rated V_{CES} , V_{EB} = 0) T_{C} = 125°C T_{C} = 125°C T_{C} = 125°C	ICES	_ _ _		100 500 100	μAdc

⁽¹⁾ Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.

Emitter Cutoff Current (VEB = 9.0 Vdc, IC = 0)

(2) Proper strike and creepage distance must be provided.

μAdc (continued)

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Designer's and SWITCHMODE are trademarks of Motorola, Inc.

REV 1

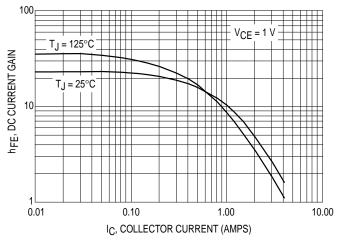


100

MJE18002 MJF18002

ELECTRICAL CHAR		Characteristic		<u> </u>	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTIC	s				<u> </u>			ı	
Base–Emitter Saturation Voltage ($I_C = 0.4 \text{ Adc}$, $I_B = 40 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 0.2 \text{ Adc}$)				V _{BE(sat)}	_ _	0.825 0.92	1.1 1.25	Vdc	
Collector–Emitter Saturation Voltage (I _C = 0.4 Adc, I _B = 40 mAdc) @ T _C = 125°C				VCE(sat)		0.2 0.2	0.5 0.5	Vdc	
$(I_C = 1.0 \text{ Adc}, I_B = 0)$	0.2 Add	c)		@ T _C = 125°C		_ _	0.25 0.3	0.5 0.6	
DC Current Gain (I _C =	= 0.2 A	dc, V _{CE} = 5.0 Vdc)		0.7	h _{FE}	14	_	34	_
(I _C =	= 0.4 A	dc, V _{CE} = 1.0 Vdc)		$@ T_C = 125^{\circ}C$		<u> </u>	27 17	_	
(IC =	= 1.0 A	dc, V _{CE} = 1.0 Vdc)		@ T _C = 125°C		11 6.0	20 8.0	_ _	
(IC =	= 10 m/	Adc, V _{CE} = 5.0 Vdc)		$@ T_C = 125^{\circ}C$		5.0 10	8.0 20	_	
DYNAMIC CHARACTE			<u> </u>						
Current Gain Bandwid	th (IC	= 0.2 Adc, V _{CE} = 10) Vdc, f = 1	.0 MHz)	fΤ	_	13	_	MHz
Output Capacitance (V _{CB} =	10 Vdc, I _E = 0, f = 1	.0 MHz)		C _{ob}	_	35	60	pF
Input Capacitance (VE	B = 8.	0 V)			C _{ib}	_	400	600	pF
Dynamic Saturation:		I _C = 0.4 A	1.0 μs	@ T _C = 125°C	VCE(dsat)	_ _	3.5 8.0	_ _	Vdc
determined 1.0 μs a 3.0 μs after rising I _E reach 0.9 final I _{B1}		$I_{B1} = 40 \text{ mA}$ $V_{CC} = 300 \text{ V}$	3.0 μs	@ T _C = 125°C		_	1.5 3.8	_	
(see Figure 18)		I _C = 1.0 A	1.0 μs	@ T _C = 125°C		_	8.0 14	_	
		I _{B1} = 0.2 A V _{CC} = 300 V	3.0 μs	@ T _C = 125°C			2.0 7.0	_	
SWITCHING CHARAC	TERIS	TICS: Resistive Loa	u ad (D.C. ≤		i = 20 ແs)	ı	ı	ı	
Turn-On Time	I _C =	0.4 Adc	(ton	_	200	300	ns
Turn–Off Time		= 40 mAdc = 0.2 Adc		@ T _C = 125°C	+ "	_	130 1.2		110
Tuni On Time) = 300 V		@ T _C = 125°C	^t off	_	1.5	2.5 —	μs
Turn-On Time	I _{B1} :	1.0 Adc = 0.2 Adc		@ T _C = 125°C	t _{on}	_ _	85 95	150 —	ns
Turn-Off Time	I _{B2} = 0.5 Adc V _{CC} = 300 V		@ T _C = 125°C	^t off	_ _	1.7 2.1	2.5 —	μs	
SWITCHING CHARAC	TERIS	TICS: Inductive Loa	ad (V _{clam)}	o = 300 V, V _{CC} =	15 V, L = 200 μl	- 1)			
Fall Time	IC	= 0.4 Adc, I_{B1} = 40 I_{B2} = 0.2 Adc	mAdc,	@ T _C = 125°C	^t fi	_ _	125 120	200 —	ns
Storage Time				@ T _C = 125°C	t _{si}	_	0.7 0.8	1.25 —	μs
Crossover Time			@ T _C = 125°C	t _C	_ _	110 110	200 —	ns	
Fall Time	I _{B2} = 0.5 Adc			@ T _C = 125°C	^t fi	_ _	110 120	175 —	ns
Storage Time				@ T _C = 125°C	^t si	_ _	1.7 2.25	2.75 —	μs
Crossover Time				@ T _C = 125°C	t _C	_	200 250	300 —	ns
Fall Time	$I_C = 0.4$ Adc, $I_{B1} = 50$ mAdc, $I_{B2} = 50$ mAdc			@ T _C = 125°C	t _{fi}	_ _	140 185	200 —	ns
Storage Time				@ T _C = 125°C	^t si		2.2 2.5	3.0 —	μs
Crossover Time			@ T _C = 125°C	t _C	_ 	140 220	250 —	ns	

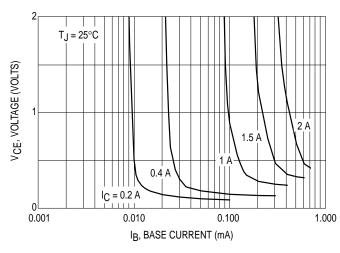
TYPICAL STATIC CHARACTERISTICS



T_J = 125°C T_J = 25°C V_{CE} = 5 V T_J = 20°C T_J = 20°C T_J = 20°C T_J = 10.00 T_C, COLLECTOR CURRENT (AMPS)

Figure 1. DC Current Gain @ 1 Volt

Figure 2. DC Current Gain @ 5 Volts



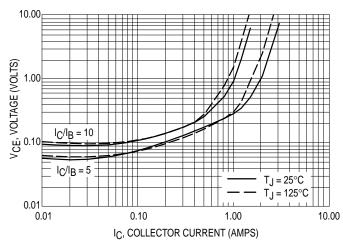
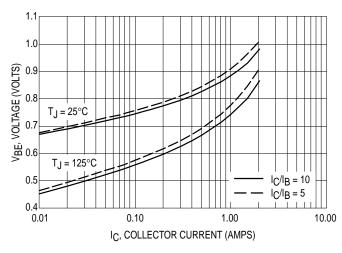


Figure 3. Collector Saturation Region

Figure 4. Collector-Emitter Saturation Voltage



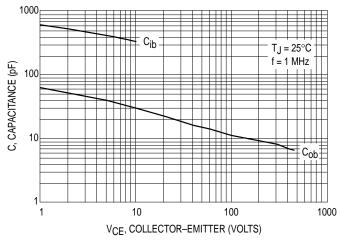
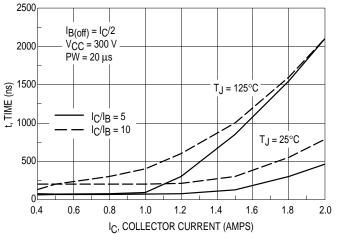


Figure 5. Base-Emitter Saturation Region

Figure 6. Capacitance

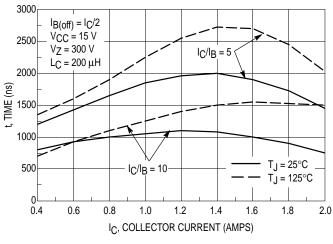
TYPICAL SWITCHING CHARACTERISTICS (IB2 = IC/2 for all switching)



4500 $I_{B(off)} = I_{C}/2$ 4000 $V_{CC} = 300 \text{ V}$ $I_C/I_B = 5$ 3500 $PW = 20 \mu s$ 3000 (ns) $T_{.J} = 25^{\circ}C$ 2500 T_J = 125°C 2000 IC/IB = 101500 1000 500 0 0.6 0.8 1.2 0.4 1.0 1.4 1.6 1.8 2.0 IC, COLLECTOR CURRENT (AMPS)

Figure 7. Resistive Switching, ton

Figure 8. Resistive Switching, toff



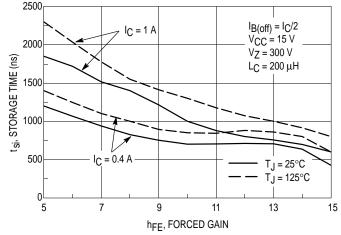
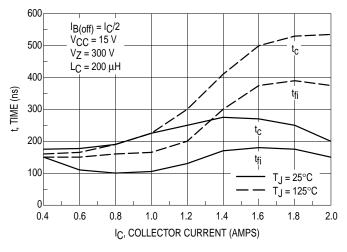


Figure 9. Inductive Storage Time, t_{Si}

Figure 10. Inductive Storage Time



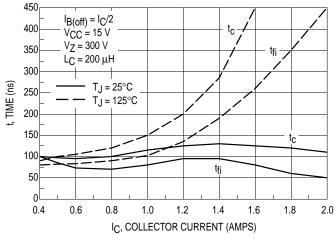
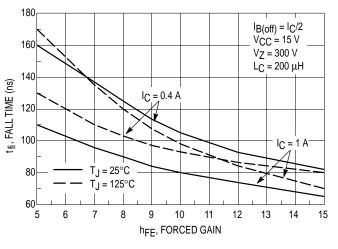


Figure 11. Inductive Switching, t_C & t_{fi}, I_C/I_B = 5

Figure 12. Inductive Switching, t_C & t_{fi}, I_C/I_B = 10

TYPICAL SWITCHING CHARACTERISTICS (IB2 = IC/2 for all switching)



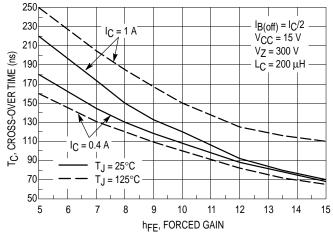


Figure 13. Inductive Fall Time

Figure 14. Inductive Crossover Time

GUARANTEED SAFE OPERATING AREA INFORMATION

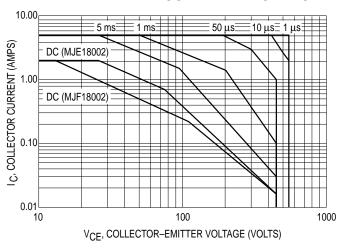


Figure 15. Forward Bias Safe Operating Area

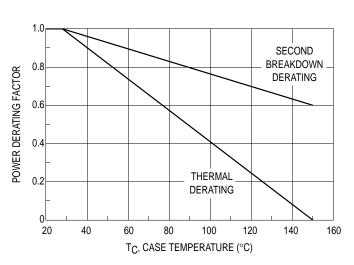


Figure 17. Forward Bias Power Derating

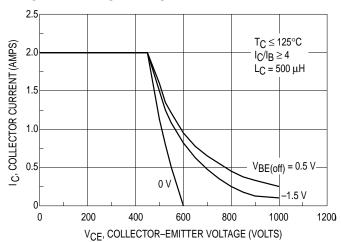
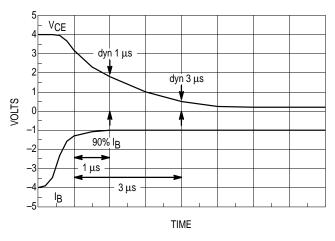


Figure 16. Reverse Bias Switching Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC-VCF limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on $T_C = 25^{\circ}C$; $T_{\perp}(pk)$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when T_C > 25°C. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17. T_J(pk) may be calculated from the data in Figures 20 and 21. At any case temperatures, thermal limitations will reduce the power that can be handled to values less the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base to emitter junction reverse biased. The safe level is specified as a reverse biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

MJE18002 MJF18002



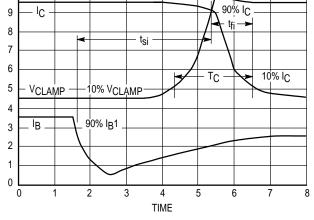
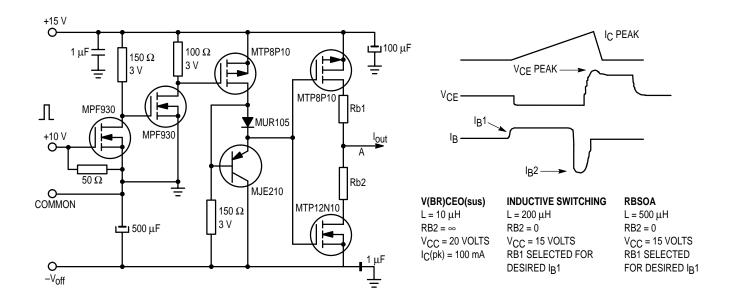


Figure 18. Dynamic Saturation Voltage Measurements

Figure 19. Inductive Switching Measurements



10

Table 1. Inductive Load Switching Drive Circuit

TYPICAL THERMAL RESPONSE

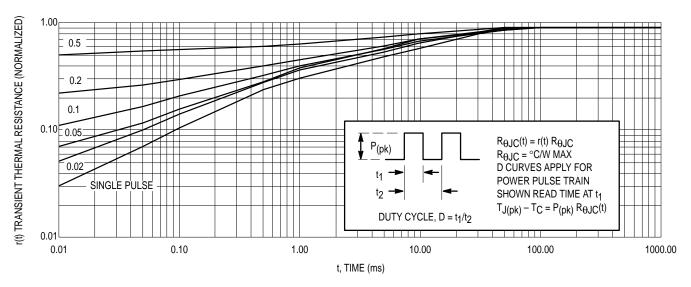


Figure 20. Typical Thermal Response (Z_{θ} JC(t)) for MJE18002

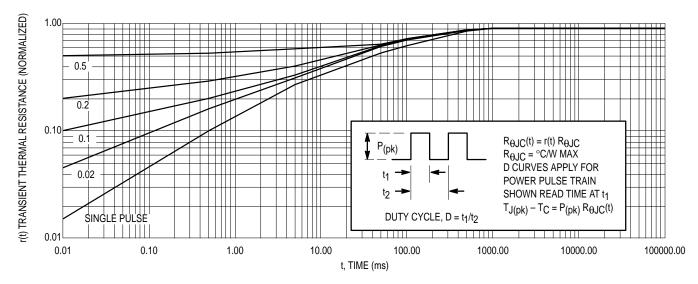
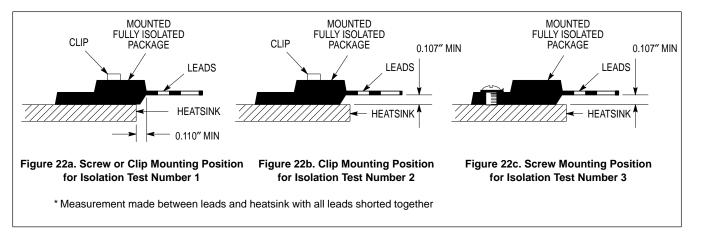


Figure 21. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJF18002

TEST CONDITIONS FOR ISOLATION TESTS*



MOUNTING INFORMATION**

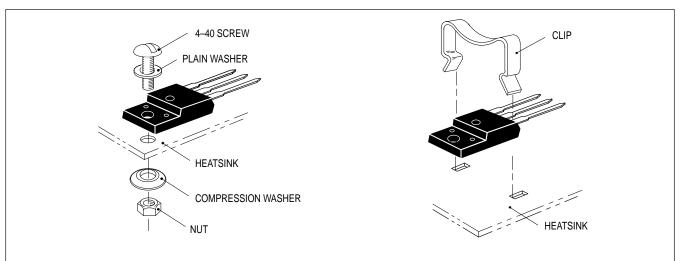


Figure 23a. Screw-Mounted

Figure 23b. Clip-Mounted

Figure 23. Typical Mounting Techniques for Isolated Package

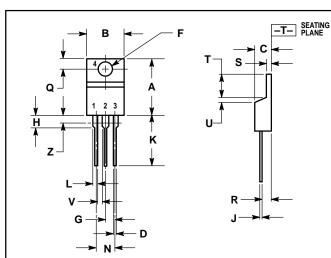
Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in • lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in • lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, Motorola does not recommend exceeding 10 in • lbs of mounting torque under any mounting conditions.

^{**} For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS

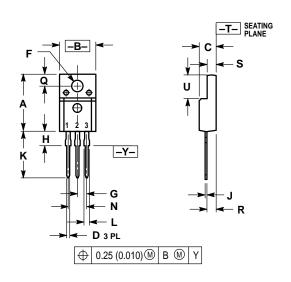


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 1: PIN 1. BASE
 - 2. COLLECTOR 3. EMITTER
 - COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MIN MAX		MAX	
Α	0.621	0.629	15.78	15.97	
В	0.394	0.402	10.01	10.21	
С	0.181	0.189	4.60	4.80	
D	0.026	0.034	0.67	0.86	
F	0.121	0.129	3.08	3.27	
G	0.100	BSC	2.54 BSC		
Н	0.123	0.129	3.13	3.27	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.14	1.52	
N	0.200 BSC		5.08 BSC		
Q	0.126	0.134	3.21	3.40	
R	0.107	0.111	2.72	2.81	
S	0.096	0.104	2.44	2.64	
U	0.259	0.267	6.58	6.78	

- STYLE 2: PIN 1. BASE 2. COLLECTOR 3. EMITTER

CASE 221D-02 (ISOLATED TO-220 TYPE) **UL RECOGNIZED: FILE #E69369 ISSUE D**

MJE18002 MJF18002

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and (M) are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3–14–2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



